Hex Gate

The MC14572UB hex functional gate is constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These complementary MOS logic gates find primary use where low power dissipation and/or high noise immunity is desired. The chip contains four inverters, one NOR gate and one NAND gate.

Features

- Diode Protection on All Inputs
- Single Supply Operation
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- NOR Input Pin Adjacent to V_{SS} Pin to Simplify Use As An Inverter
- NAND Input Pin Adjacent to V_{DD} Pin to Simplify Use As An Inverter
- NOR Output Pin Adjacent to Inverter Input Pin For OR Application
- NAND Output Pin Adjacent to Inverter Input Pin For AND Application
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load over the Rated Temperature Range
- Pb-Free Packages are Available*

MAXIMUM RATINGS (Voltages Referenced to VSS)

Parameter	Symbol	Value	Unit
DC Supply Voltage Range	V_{DD}	-0.5 to +18.0	V
Input or Output Voltage Range (DC or Transient)	V _{in} , V _{out}	-0.5 to V _{DD} + 0.5	V
Input or Output Current (DC or Transient) per Pin	I _{in} , I _{out}	±10	mA
Power Dissipation, per Package (Note 1)	P _D	500	mW
Ambient Temperature Range	T _A	-55 to +125	°C
Storage Temperature Range	T _{stg}	-65 to +150	°C
Lead Temperature (8–Second Soldering)	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 Temperature Derating: Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



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MARKING DIAGRAMS



PDIP-16 P SUFFIX CASE 648 

SOIC-16 D SUFFIX CASE 751B 16 ______ 14572UBG O AWLYWW



SOEIAJ-16 F SUFFIX CASE 966 A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G = Pb-Free Package

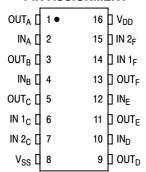
ORDERING INFORMATION

Device	Package	Shipping [†]
MC14572UBCP	PDIP-16	25 Units / Rail
MC14572UBCPG	PDIP-16 (Pb-Free)	25 Units / Rail
MC14572UBD	SOIC-16	48 Units / Rail
MC14572UBDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14572UBDR2	SOIC-16	2500/Tape & Reel
MC14572UBDR2G	SOIC-16 (Pb-Free)	2500/Tape & Reel
MC14572UBF	SOEIAJ-16	50 Units / Rail

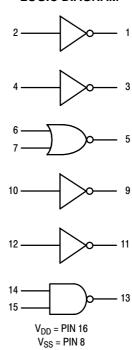
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

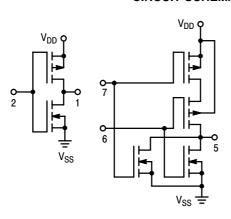
PIN ASSIGNMENT

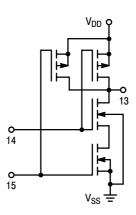


LOGIC DIAGRAM



CIRCUIT SCHEMATIC





$\textbf{ELECTRICAL CHARACTERISTICS} \ (\textit{Voltages Referenced to V}_{SS})$

			- 5	5°C		25°C		125	5°C	
Characteristic	Symbol	V _{DD} Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage "0" Level $V_{in} = V_{DD}$ or 0	V _{OL}	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
$V_{in} = 0 \text{ or } V_{DD}$ "1" Level	V _{OH}	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage "0" Level (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc)	V _{IL}	5.0 10 15	- - -	1.0 2.0 2.5	_ _ _	2.25 4.50 6.75	1.0 2.0 2.5	- - -	1.0 2.0 2.5	Vdc
"1" Level (V _O = 0.5 or 4.5 Vdc) (V _O = 1.0 or 9.0 Vdc) (V _O = 1.5 or 13.5 Vdc)	V _{IH}	5.0 10 15	4.0 8.0 12.5	- - -	4.0 8.0 12.5	2.75 5.50 8.25	_ _ _	4.0 8.0 12.5	_ _ _	Vdc
Output Drive Current (V _{OH} = 2.5 Vdc) Source (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc)	I _{OH}	5.0 5.0 10 15	- 1.2 - 0.25 - 0.62 - 1.8	- - - -	- 1.0 - 0.2 - 0.5 - 1.5	- 1.7 - 0.36 - 0.9 - 3.5	- - - -	- 0.7 - 0.14 - 0.35 - 1.1	- - - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ Sink $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	I _{OL}	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current	I _{in}	15	-	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc
Input Capacitance (V _{in} = 0)	C _{in}	_	-	-	_	5.0	7.5	_	-	pF
Quiescent Current (Per Package)	I _{DD}	5.0 10 15	- - -	0.25 0.5 1.0	- - -	0.0005 0.0010 0.0015	0.25 0.5 1.0	- - -	7.5 15 30	μAdc
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Package) (C _L = 50 pF on all outputs, all buffers switching)	I _T	5.0 10 15			$I_{T} = (3$.89 μΑ/kHz) 3.80 μΑ/kHz) 3.68 μΑ/kHz)	f + I _{DD}			μAdc

Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25°C.
 To calculate total supply current at loads other than 50 pF: I_T(C_L) = I_T(50 pF) + (C_L – 50) Vfk where: I_T is in μA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.006.

SWITCHING CHARACTERISTICS (Type 5) ($C_L = 50 \text{ pF}, T_A = 25^{\circ}C$)

Characteristic	Symbol	V _{DD}	Min	Typ (Note 6)	Max	Unit
Output Rise Time $t_{TLH} = (3.0 \text{ ns/pF}) C_L + 30 \text{ ns}$ $t_{TLH} = (1.5 \text{ ns/pF}) C_L + 15 \text{ ns}$ $t_{TLH} = (1.1 \text{ ns/pF}) C_L + 10 \text{ ns}$	t _{TLH}	5.0 10 15	- - -	180 90 65	360 180 130	ns
Output Fall Time $t_{THL} = (1.5 \text{ ns/pF}) C_L + 25 \text{ ns}$ $t_{THL} = (0.75 \text{ ns/pF}) C_L + 12.5 \text{ ns}$ $t_{THL} = (0.55 \text{ ns/pF}) C_L + 9.5 \text{ ns}$	t _{THL}	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time t_{PLH} , $t_{PHL} = (1.7 \text{ ns/pF}) C_L + 5 \text{ ns}$ t_{PLH} , $t_{PHL} = (0.66 \text{ ns/pF}) C_L + 17 \text{ ns}$ t_{PLH} , $t_{PHL} = (0.5 \text{ ns/pF}) C_L + 15 \text{ ns}$	t _{PLH} , t _{PHL}	5.0 10 15	- - -	90 50 40	180 100 80	ns

- 5. The formulas given are for the typical characteristics only at 25°C.
 6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

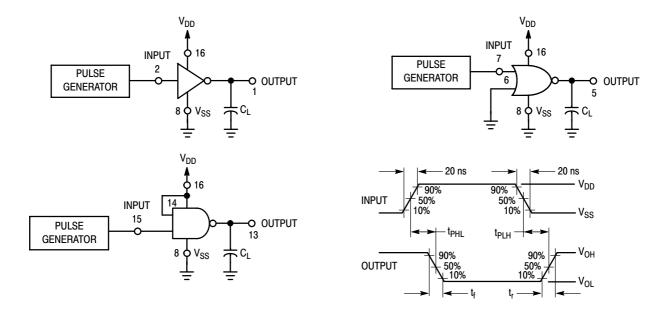
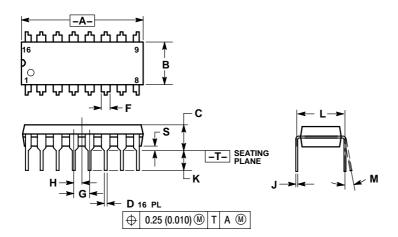


Figure 1. Switching Time Test Circuits and Waveforms

PACKAGE DIMENSIONS

PDIP-16 CASE 648-08 **ISSUE T**

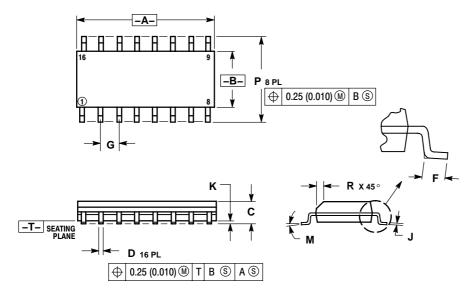


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE
- MOLD FLASH.

 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
C	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54 BSC		
Н	0.050	BSC	1.27	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
М	0°	10 °	0°	10 °	
S	0.020	0.040	0.51	1.01	

SOIC-16 CASE 751B-05 **ISSUE J**



NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

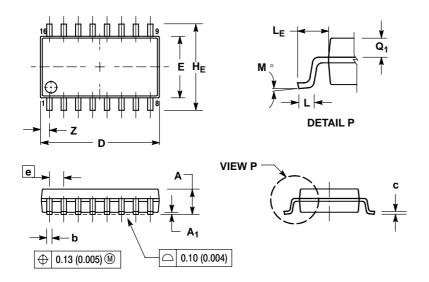
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006)

- 4. MAXIMUM MOLLD PHOTHUSION 0.15 (0.000)
 PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES			
DIM	MIN	MAX	MIN	MAX		
Α	9.80	10.00	0.386	0.393		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27	BSC	0.050	0.050 BSC		
J	0.19	0.25	0.008	0.009		
K	0.10	0.25	0.004	0.009		
M	0°	7°	0°	7°		
P	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		

PACKAGE DIMENSIONS

SOEIAJ-16 CASE 966-01 ISSUE A



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14 5M 1982
- 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE
 MOLD FLASH OR PROTRUSIONS AND ARE
 MEASURED AT THE PARTING LINE. MOLD FLASH
 OR PROTRUSIONS SHALL NOT EXCEED 0.15
 (0.006) PER SIDE.

 TERMINAL NUMBERS ARE SHOWN FOR
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT
- 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α		2.05		0.081	
Α ₁	0.05	0.20	0.002	0.008	
b	0.35	0.50	0.014	0.020	
C	0.10	0.20	0.007	0.011	
D	9.90	10.50	0.390	0.413	
Е	5.10	5.45	0.201	0.215	
е	1.27	BSC	0.050 BSC		
HE	7.40	8.20	0.291	0.323	
L	0.50	0.85	0.020	0.033	
LΕ	1.10	1.50	0.043	0.059	
M	0 °	10°	0 °	10°	
Q ₁	0.70	0.90	0.028	0.035	
Z		0.78		0.031	

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